

N-Channel Power MOSFET

800V, 4A, 3.0Ω

FEATURES

- Low $R_{DS(ON)}$ 3 Ω (Max.)
- Low gate charge typical @ 20nC (Typ.)
- Improve dV/dt capability

KEY PERFORMANCE PARAMETERS				
PARAMETER	R VALUE UNIT			
V _{DS}	800	V		
R _{DS(on)} (max)	3.0	Ω		
Q_g	20	nC		

APPLICATION

Power Supply

Lighting





ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)				
PARAMETER	SYMBOL	TO-220	ITO-220	UNIT
Drain-Source Voltage	V_{DS}	800		V
Gate-Source Voltage	V_{GS}	±	30	V
Continuous Drain Current (Note 4) T _C = 25°C			4	
T _C = 100°C	I _D	2.5		Α
Pulsed Drain Current (Note 2)	I_{DM}	16		Α
Total Power Dissipation @ T _C = 25°C	P_{DTOT}	123	38.7	W
Single Pulsed Avalanche Energy (Note 3)	E_{AS}	7	' 6	mJ
Single Pulsed Avalanche Current (Note 3)	I_{AS}		4	Α
Repetitive Avalanche Energy	E_AR	12	2.3	mJ
Peak Diode Recovery ^(Note 7)	dV/dt	4	.5	V
Operating Junction and Storage Temperature Range	T_J , T_{STG}	- 55 to	o +150	°C

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	TO-220	ITO-220	UNIT
Junction to Case Thermal Resistance	R _{eJC}	1.01	3.23	°C/W
Junction to Ambient Thermal Resistance	R _{OJA}	62.5		°C/W

Notes: $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. $R_{\Theta JA}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design. $R_{\Theta JA}$ shown below for single device operation on FR-4 PCB in still air.



ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 4)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	800			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	2.0		4.0	V
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	I _{GSS}		-	±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 700V, V_{GS} = 0V$	I _{DSS}		🛦	10	μΑ
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 1.2A$	R _{DS(on)}		2.5	3.0	Ω
Forward Transconductance	$V_{DS} = 30V, I_{D} = 1.2A$	g fs		7.1	<u></u>	S
Dynamic (Note 5)			1			
Total Gate Charge	.,	Q_g	(20		
Gate-Source Charge	$V_{DS} = 640V, I_D = 4.0A,$	Q_{gs}		3.7		nC
Gate-Drain Charge	V _{GS} = 10V	Q _{gd}	į	8.2		
Input Capacitance	.,	C _{iss}	J	955		
Output Capacitance	$V_{DS} = 25V$, $V_{GS} = 0V$, $f = 1.0MHz$	Coss		80		pF
Reverse Transfer Capacitance		C _{rss}		13		
Gate Resistance	F = 1MHz, open drain	R_g			3	Ω
Switching (Note 6)						
Turn-On Delay Time		t _{d(on)}		49		
Turn-On Rise Time	$V_{DD} = 400V,$ $R_{GEN} = 25\Omega,$ $I_{D} = 4.0A, V_{GS} = 10V,$	t _r		38		
Turn-Off Delay Time		t _{d(off)}		146		ns
Turn-Off Fall Time		t _f		50		
Source-Drain Diode (Note 4)						
Forward On Voltage	$I_{S} = 4.0A, V_{GS} = 0V$	V _{SD}			1.5	V
Reverse Recovery Time	$V_{GS} = 0V, I_{S} = 4A$	t _{rr}		487		ns
Reverse Recovery Charge	$dI_F/dt = 100A/\mu s$	Q _{rr}		2.8		μC

Notes:

- 1. Current limited by package
- 2. Pulse width limited by the maximum junction temperature
- 3. L = 10mH, I_{AS} = 4.0A, V_{DD} = 50V, R_G = 25 Ω , Starting T_J = 25 $^{\circ}$ C
- 4. Pulse test: PW ≤ 300µs, duty cycle ≤ 2%
- 5. For DESIGN AID ONLY, not subject to production testing.
- 6. Switching time is essentially independent of operating temperature.
- 7. $I_{SD} \le 8A$, $dI/dt \le 200A/uS$, $Vdd \le BV_{DSS}$, Starting $T_J = 25^{\circ}C$.



ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSM4N80CZ C0G	TO-220	50pcs / Tube
TSM4N80CI C0G	ITO-220	50pcs / Tube

Note:

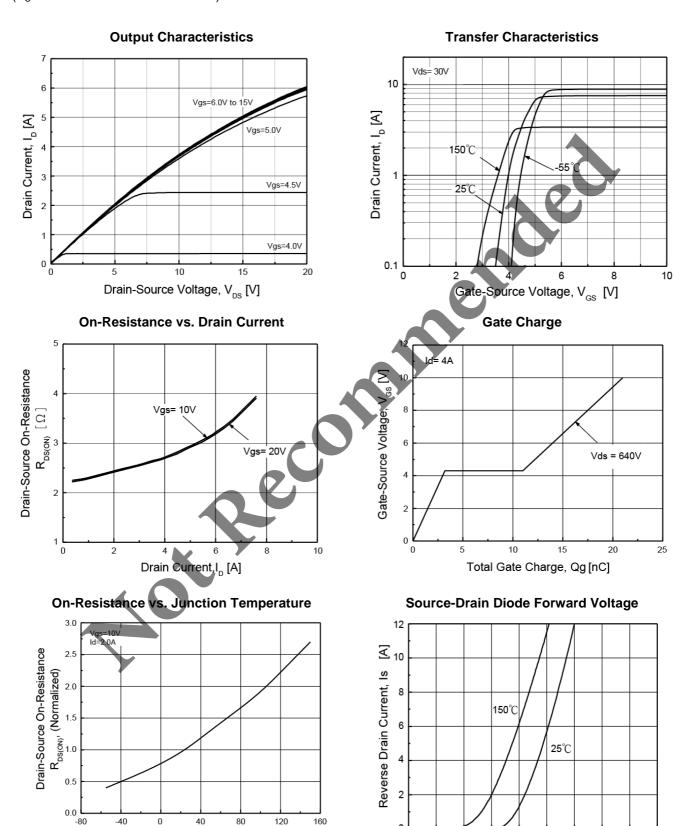
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition





CHARACTERISTICS CURVES

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$



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Junction Temperature, T_J [°C]

0.0 0.2 1.6

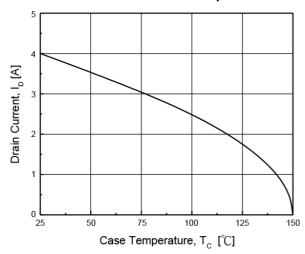
0.4 0.6 0.8 1.0 1.2 1.4 Source-Drain Voltage, V_{SD} [V]



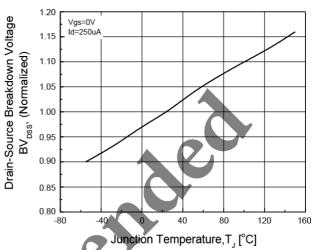
CHARACTERISTICS CURVES

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$

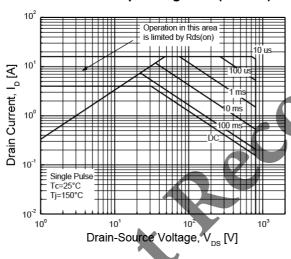
Drain Current vs. Case Temperature



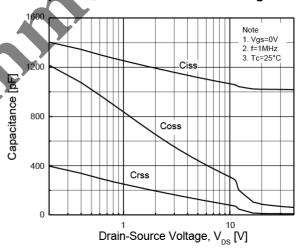
BV_{DSS} vs. Junction Temperature



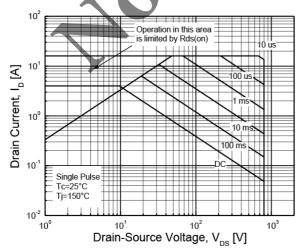
Maximum Safe Operating Area (TO-220)



Capacitance vs. Drain-Source Voltage



Maximum Safe Operating Area (ITO-220)

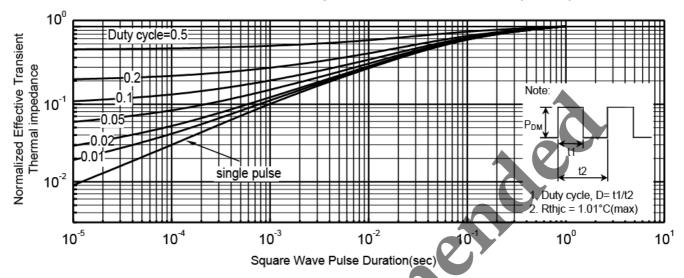




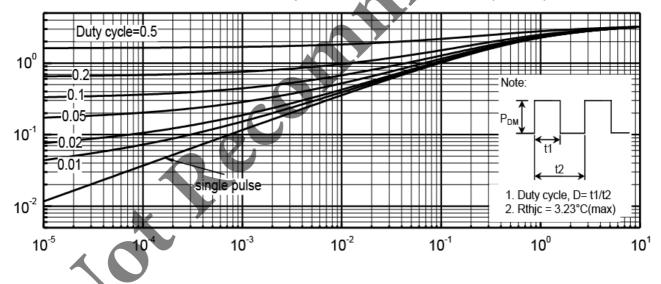
CHARACTERISTICS CURVES

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$

Normalized Thermal Transient Impedance, Junction-to-Ambient (TO-220)



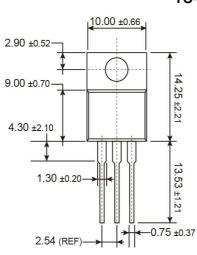
Normalized Thermal Transient Impedance, Junction-to-Ambient (ITO-220)

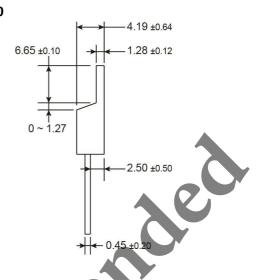




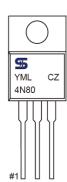
PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)







MARKING DIAGRAM



Y = Year Code

M = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar

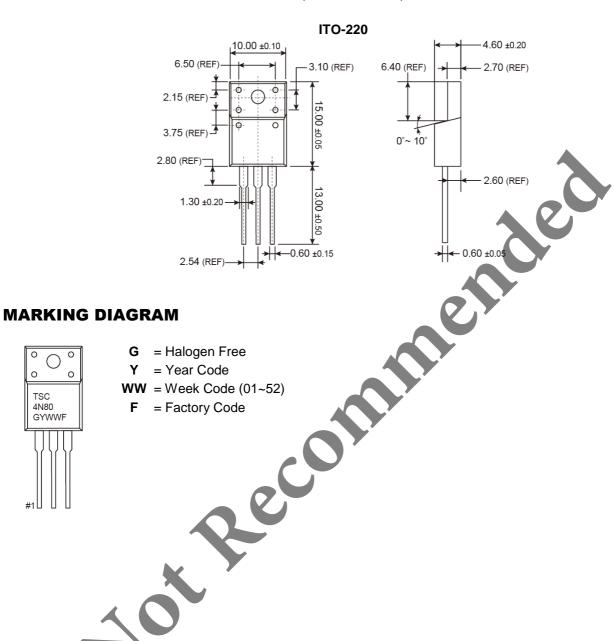
S =May T =Jun U =Jul V ≠Aug

W =Sep X =Oct Y =Nov Z =Dec

L = Lot Code (1~9, A~Z)



PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

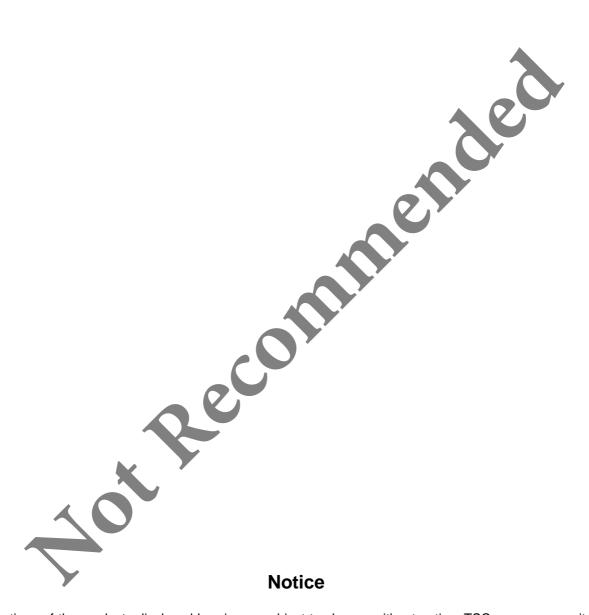


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